Title: METHOD FOR MANUFACTURING SINGLE CRYSTAL SEMICONDUCTOR (Masafumi URA et al.) Filed: 8/7/2006
Attorney Docket No.: 1110/97962 (SHEET 1 OF 5)

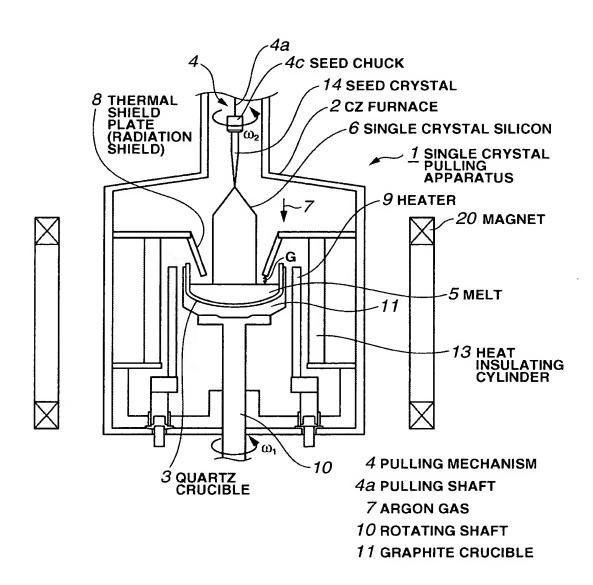


FIG.1

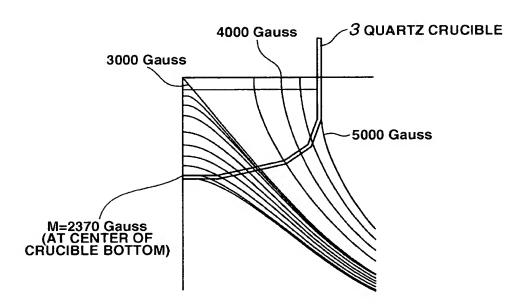


FIG.2

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RESULT	0	0	0	0	0	0	0	0	×	×	×	×	×	×	×	×
CRYSTAL PERIPHERAL VELOCITY (m/sec)	0.141	0.157	0.157	0.141	0.141	0.126	0.126	0.157	0.084	0.126	0.141	0.136	0.157	0.110	0.126	0.157
CRYSTAL ROTATING VELOCITY (rpm)	13.5	10.0	10.0	9.0	13.5	12.0	8.0	10.0	8.0	12.0	13.5	13.0	10.0	7.0	8.0	10.0
M/V <sup>1/3</sup>	40.4	40.3	48.4	56.4	42.6	56.1	35.5	61.3	15.7	15.7	33.6	89.7	32.2	48.4	64.5	64.5
MAGNETIC FIELD STRENGTH M (Gauss)	1497	1975	2370	2765	1580	2079	1738	3002	582	582	1247	3326	1580	2370	3160	3160
CRYSTAL DIAMETER (mm)	200	300	300	300	200	200	300	300	200	200	200	200	300	300	300	300
STANDARD No.	-	2	က	4	5	9	7	8	တ	10	11	12	13	14	15	16

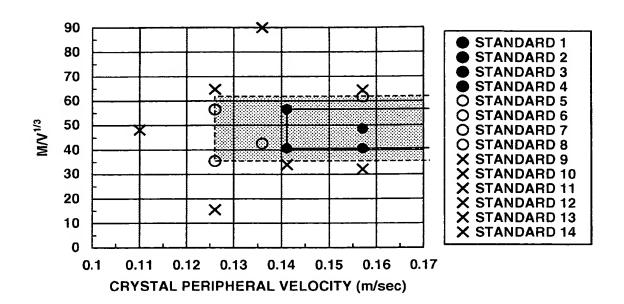


FIG.4

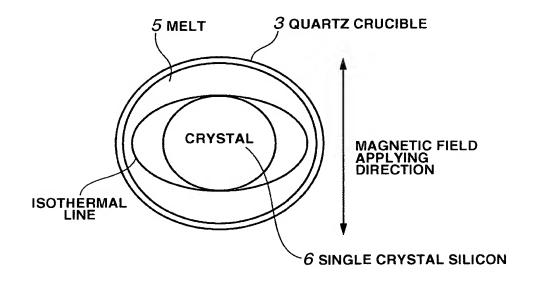


FIG.5

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X-RAY PHOTOS OF CRYSTAL CROSS SECTION

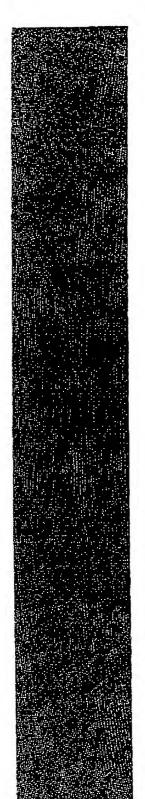


FIG.6(a) DISTANCE BETWEEN GROWTH STRIATIONS IS UNIFORM, © AND STRIATIONS ARE DENSE AND LIGHT.

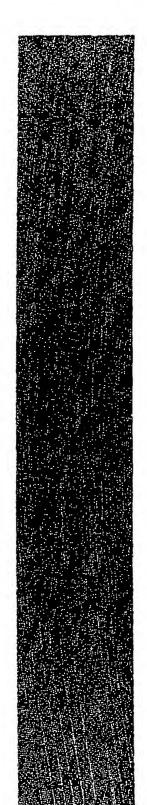


FIG.6(b) DISTANCE BETWEEN GROWTH STRIAITONS OF IS SOMEWHAT NONUNIFORM.

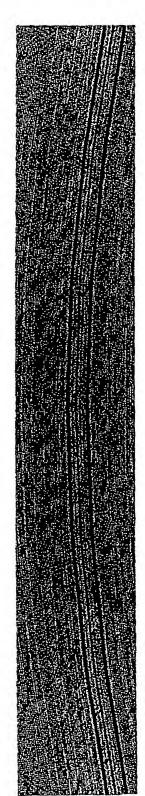


FIG.6(c) DISTANCE BETWEEN GROWTH STRIAITONS IS NOT UNIFORM AND STRIATIONS ARE DARK.

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